

Rev.A Jun.-2025

SOT-23 P MOS

P- CHANNEL MOSFET in a SOT-23 Plastic Package.

$V_{DS} = -20V$ $I_D = -5.3A$

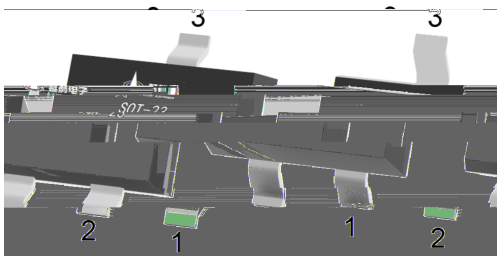
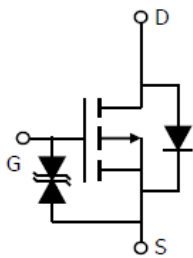
$R_{DS(on)} @ -4.5V \leq 33.2m\Omega$, (Typ. 25.5m Ω)

$R_{DS(on)} @ -2.5V \leq 46.8m\Omega$, (Typ. 35.2m Ω)

ESD Protected

HF Product.

Load switch Battery protection.



PIN1 G

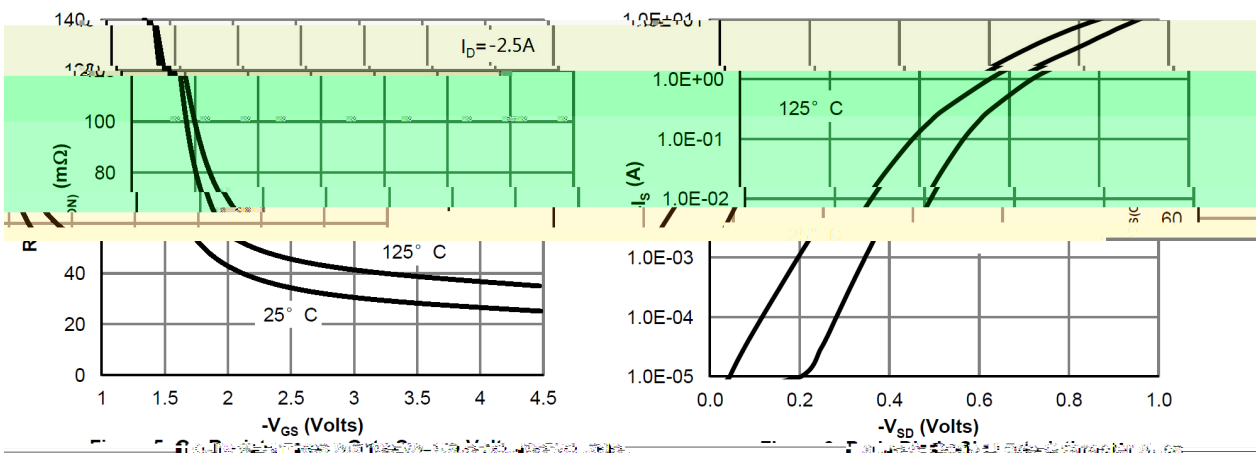
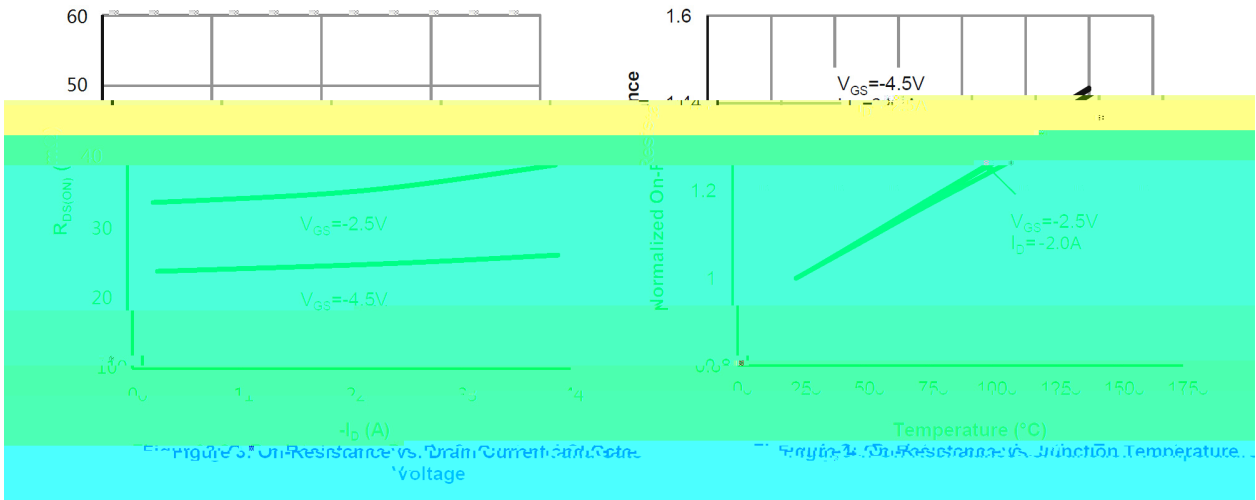
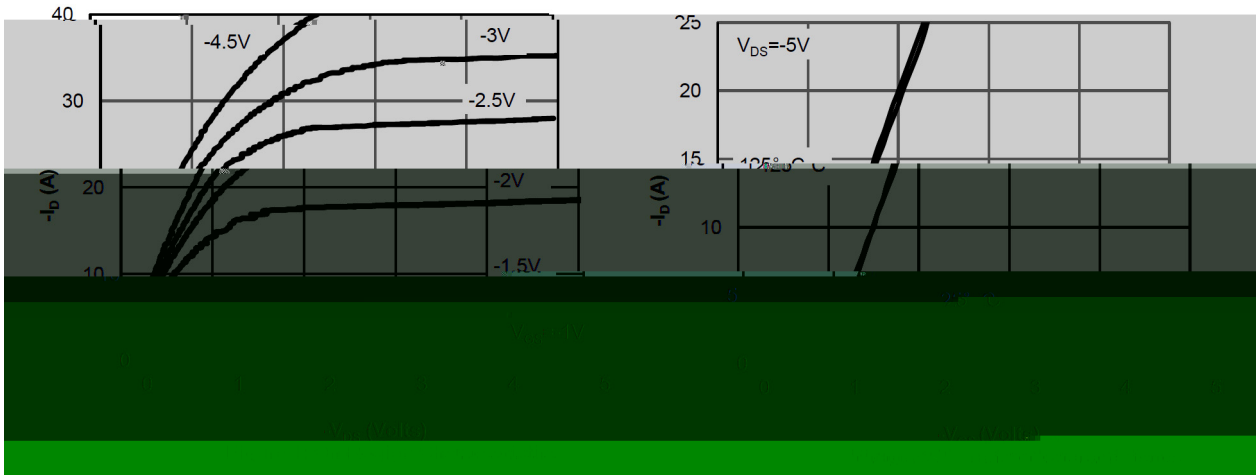
PIN 2 S

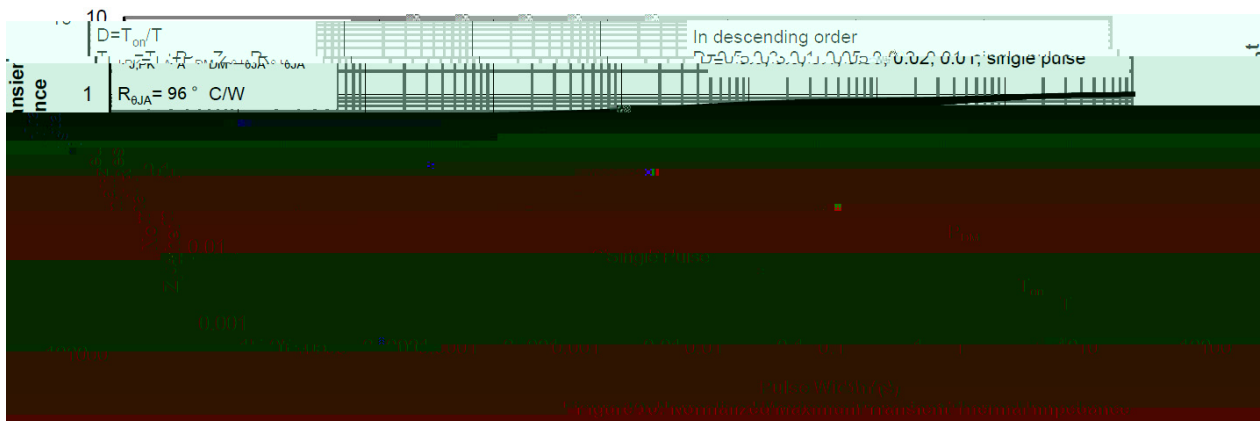
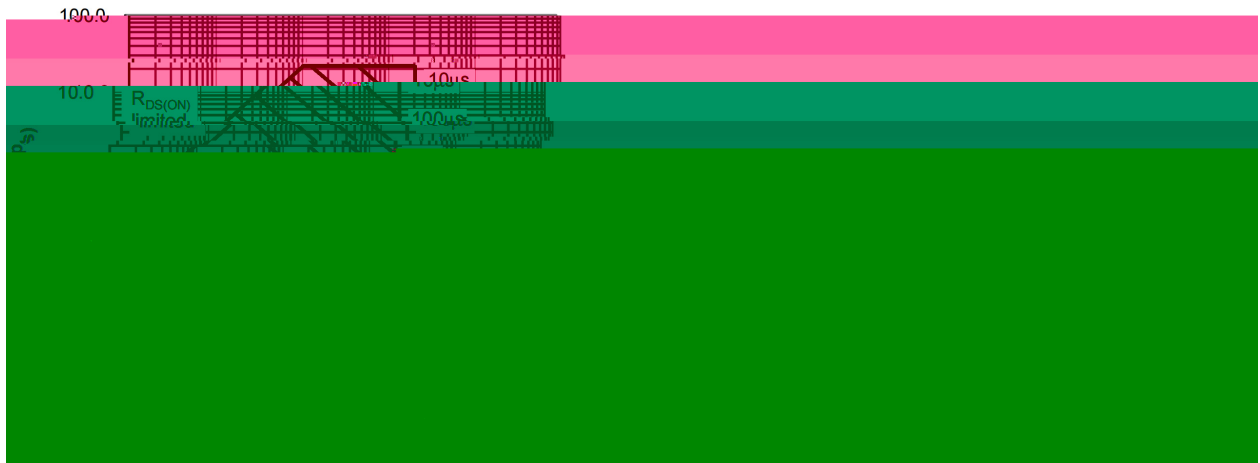
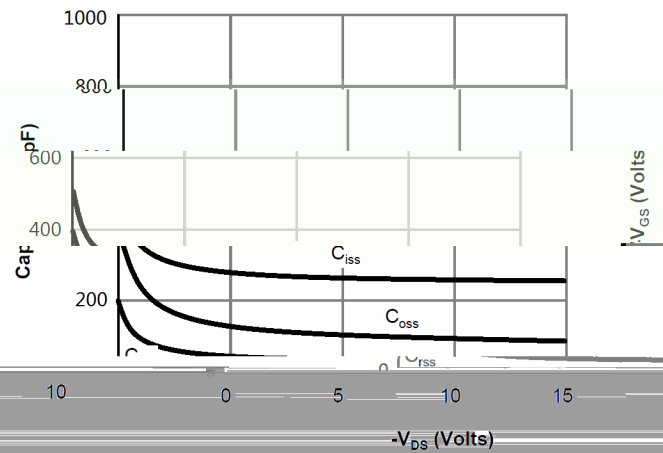
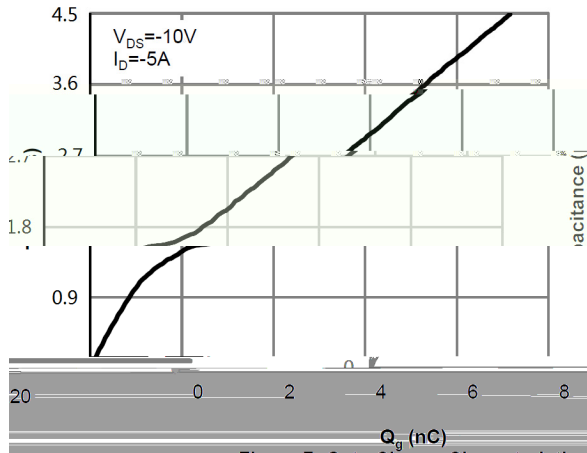
PIN 3 D

Marking	AFH
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Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-5.3	A
Drain Current-Continuous($T_A = 100^\circ\text{C}$)	I_D	-3.3	A
Drain Current-Pulsed	I_{DM}	-21.2	A
Maximum Power Dissipation	P_D	1.3	W
Maximum Power Dissipation($T_A = 100^\circ\text{C}$)	P_D	0.5	W
Operating Junction Temperature Range and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	96	$^\circ\text{C/W}$

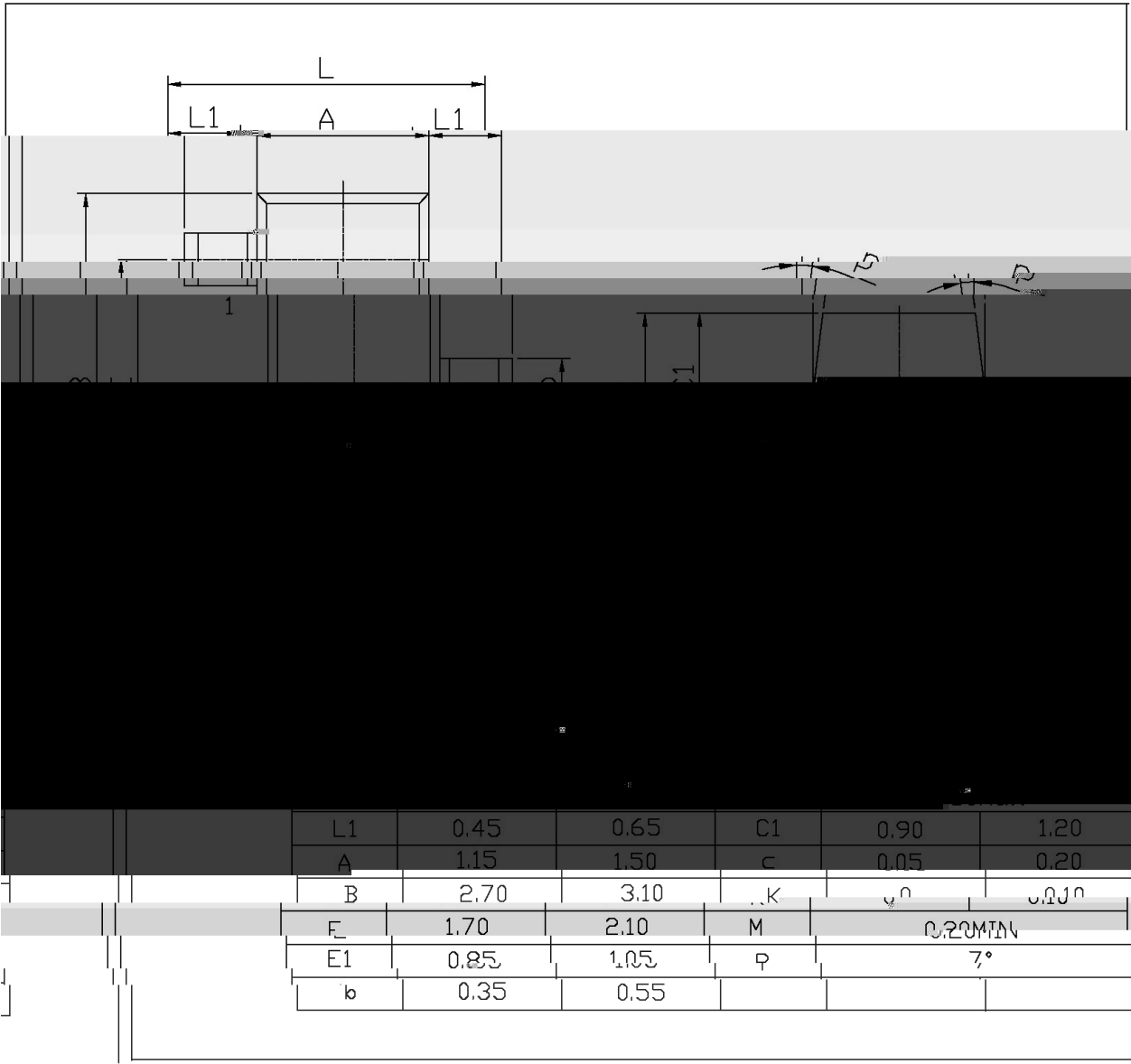
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$B_{V_{DS}}$	$V_{GS}=0V \quad I_D = -250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V \quad V_{GS}=0V$			-1	μA
Gate-Body Leakage	I_{GSS}	$V_{GS}=\pm 10V \quad V_{DS}=0V$			± 10	μA
Gate Threshold Voltage	V_{TH}	$V_{DS}=V_{GS} \quad I_D=-250\mu A$ $V_{GS}=-4.5V \quad I_D=-2.5A$	-0.5		-1.0	V
Drain-Source On-State Resistance	R_{DS}					

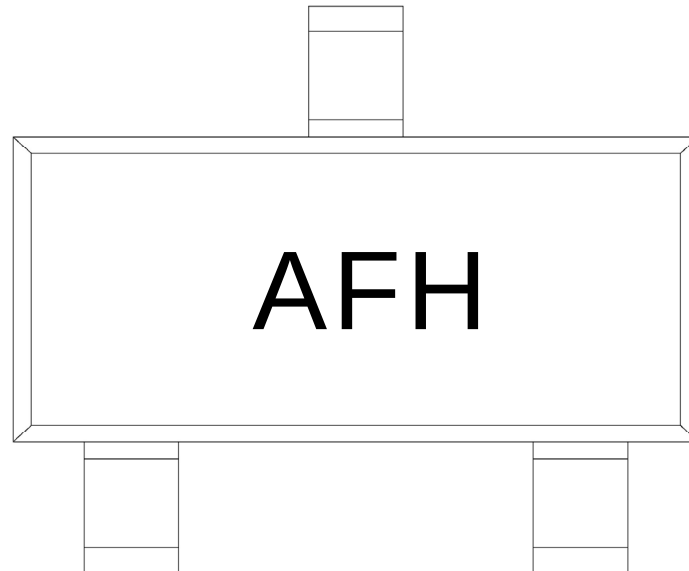




SOT-23

单位：mm





H:

AF:

Note:

H: Company Code

AF Product Type Code

Temperature Profile for IR Reflow Soldering(Pb-Free)

- 1

150 180

60 90sec;
- 2

245±5

5±0.5sec;
- 3

2 10 /sec.
- Note:

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5℃

Time:10±1 sec

/ REEL